



# The Impact of MEMS-based RF Multiplexers for Next-Generation Test Systems

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The Impact of MEMS-based RF Multiplexers for Next-Generation Test Systems Panelists

### The Impact of MEMS-based RF Multiplexers for Next-Generation



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**Test Systems** 



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Organized by:







### How Ideal Switch® Works – The Unit Cell

Technology platform with breakthrough innovations in materials and processing



#### **Unique Glass Packaging**

Improved RF & thermal performances High RF power handling

#### Through-Glass-Via

Low parasitics and resistance Small-size package

#### **High Reliability**

>3B switching cycles Hermetic-sealed package

#### Scalability

50µm x 50µm (unit cell)

Scalable switch arrays for high voltage, high current, high power



### Scalable Switch Arrays With Ideal Switch®







### Advantages of Ideal Switch®



- High RF power handling up to 25 W (CW) /150 W (Pulsed)
- vs solid-state
- Low insertion loss less than 1 dB vs solid-state
- **হ**ি VS :
  - High linearity unmatched >90 dBm IP3 vs solid-state and electromechanical
  - Fast Switching less than 20 µs vs electromechanical
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- Long life minimum 3 billion switch cycles vs electromechanical
- Low DC power from 0.1 mW to less than 10 mW vs electromechanical and solid-state
- **Small size** from 6 mm<sup>2</sup> to 22 mm<sup>2</sup> footprint vs electromechanical





### Product Portfolio – High Frequency









	RF & Microwave			High-Speed Digital		
Model	MM5130	MM5120	MM5140	MM5600	MM5620	MM5622
Markets	Telecommunication, Wireless Aerospace & Defense, Test & Measurements			Semiconductor Test & Measurement, Automated Test Equipment, Aerospace & Defense Equipment		
Applications	Tunable & Programmable Filters, High-Power Low-Loss RF Switch Matrices, Programmable RF Beam Steering			High-Speed Digital SoC Loopback Testing, PCIe, DDR5, MIPI, USB-C, High-Speed Ethernet		
Switch Type	SP4T			DPDT	2x DP3T Diff AC Coupled	2x DP3T Diff DC Coupled
Frequency Range	DC – 26 GHz	DC – 18 GHz	DC – 8 GHz	40 Gbps	64 Gbps	64 Gbps
RF Power	25 W (CW), 150 W (pulsed)					
Insertion Loss	0.4 dB @ 6 GHz	0.4 dB @ 6 GHz	0.3 dB @ 3 GHz	1.3 dB @ 10 GHz	2.3 dB @ 16 GHz	2.3 dB @ 16 GHz
Linearity (IP3)	>90 dBm					
Control	Direct	SPI/GPIO	SPI/GPIO	Serial to Parallel I/F	SPI/GPIO	SPI/GPIO
DC Supply	89 V (gate)	3.3 V (control), 5 V (V <sub>CP</sub> )	3.3 V (control), 5 V (V <sub>CP</sub> )	5 V (control), 89 V (gate)	3.3 V (control), 5 V (V <sub>CP</sub> )	3.3 V (control), 5 V (V <sub>CP</sub> )
Lifetime	>3B cycles			> 3B cycles		
Package	2.5 mm x 2.5 mm WLCSP	5.2 mm x 4.2 mm LGA		8 mm x 8 mm LGA	8.2 mm x 8.2 mm LGA	8.2 mm x 8.2 mm LGA
Availability	In production			In prod	Samples: Q2 2024 Production: Q3 2024	





### Product Portfolio – Signal Relay and Power







	Signal Relay	Drivers and Smart Power		
Model	MM1205	MM101	MM9200	
Markets	Test & Measurement, Wireless Charging, Scientific & Medical, Telecommunication	All	Industrial Automation, Sustainable Buildings Transport Electrification, Solid-State Circuit Breaker & Relay	
Applications	High-Density Switch Matrices, Test & Measurement, Mechanical & PhotoMOS Replacement	All	LV Industrial Controls Solid-State & Electromechanical Relay Replacements	
Switch Type	6x SPST	High voltage CP & 8- channel driver	SPST	
DC Current	1 A per channel, 2 A per device		10 A (AC or DC), 10 mΩ	
DC Carry/Standoff Voltage	30 V/100 V		300 V (AC or DC)	
Frequency Range	DC – 3 GHz			
Control	SPI/GPIO	SPI/GPIO	Direct	
DC Supply	3.3 V (control), 5 V (V <sub>CP</sub> )	3.3 V (control), 5 V (V <sub>CP</sub> )	90 V (gate)	
Lifetime	>3B cycles		1B cycles	
Package	8 mm x 8 mm LGA	5 mm x 5 mm QFN 1.6 mm x 2.4 mm WLCSP	5 mm x 5 mm WLCSP 6 mm x 6.5 mm QFN	
Availability	In production	In production	Samples: Available Production: Q4 2024	





### **Product Roadmap**

Driving and accelerating product roadmap from customers applications







### Website Resources – Menlo Micro and GlobalSpec

Additional product support and documentation on website

- Users can sign up by clicking on "Login" and then "Request Access"
- Access Menlo's product information through **GlobalSpec website**

#### https://www.globalspec.com/supplier/profile/MenloMicro





#### http://www.menlomicro.com

What's New

Video Tutorials

All Products

**RF** Switches





### MM5130 – DC to 26 GHz High Power RF Switch



- DC to 26 GHz (super-port) and 18 GHz (standardport) frequency range
- RF power 25 W (CW) to 6 GHz, 150 W (pulse)
- High linearity IP3 >90 dBm
- <0.8 dB on-state insertion loss @ 18 GHz (super port)</li>
- High reliability >3B switching cycles guarantee
- 2.5 mm x 2.5 mm WLCSP

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• Key Application: Test and measurement, aerospace & defense, tunable filters, switch filter bank, antenna tuners, phase shifters, time delay units, digital attenuators



Measured at 25C, Data is De-Embedded



### MM5120– DC to 18 GHz SP4T RF Switch

+3.3V +1.8 to +5V

VDD

Charge Pump

+ HV Driver

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GND

VIN

4x SPI/

GPIO

RFC

VDD IO

**RF4** 

RF3

RF2

RF1



- DC to 18 GHz frequency range
- RF power 25 W (CW) to 6 GHz, 150 W (pulse)
- High linearity IP3 >90 dBm
- 0.7 dB on-state insertion loss @ 12 GHz
- Integrated high-voltage driver
- High reliability >3B switching cycles
- 5.2 mm x 4.2 mm LGA
- Key Applications: Test and measurement, aerospace & defense, tunable filters, switch filter bank, antenna tuners, phase shifters, time delay units, digital attenuators, and network I/O modules, highperformance RF switching.





### MM1205 – 6 Channel SPST High Frequency Signal Relay

- DC to 3 GHz frequency range
- 1 A per channel on-state DC carry current, 2 A per package
- Up to 30 V per-channel on-state DC carry voltage
- ~1.0 Ω on-state resistance (per channel)
- RF power 25 W (CW) to 300 MHz, 2000 W (pulsed)
- Low on-state insertion loss 0.5 dB @ 3 GHz
- 17 dB input to output off-state isolation @ 3 GHz
- Switching + settling time 17 µs
- Integrated high-voltage driver
- High reliability >3B switching cycles
- 8 mm x 8 mm LGA package
- Key Applications: Test & Measurement, Broadcasting and Audio-Visual Equipment, Network I/O Relay Module

Menlo MM1205 Datasheet (menlomicro.com)



Insertion Loss / S21





### MM5620/MM5622 – 64 Gbps High-Speed Differential Switch



- Dual DP3T Differential Loopback Mode
- DC to 20 GHz range, support 64 Gbps
- Optimized for PCIe Gen 5 & 6, SerDes
- Integrated high-voltage driver
- High reliability >3B switching cycles
- 8.2 mm x 8.2 mm LGA

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- Key Application: Test and measurement
- Road map: Smaller form factor, greater than 128 GT/s

Menlo MM5620 Datasheet (menlomicro.com)



### MM5620 S-Parameter Performance (HS1 to HS2 Signal Path)





### MM5800 - 70 GHz SPDT Millimeter Wave Switch







- Single SPDT: Small WL-CSP package
- Low-loss: 0.5dB @ 40 GHz
- High Isolation: 30 dB @ 40 GHz
- High Reliability: >3B switch cycles
- Key Application: Test and measurement

### MM9200 – 300V/10A SPST Power Switch



- Low On-State resistance: < 10 m $\Omega$  over full temp range
- Off-State Contact Leakage Current: 5 pA (typical)
- Voltage standoff (AC peak or DC): 300V
- Rated continuous current (AC or DC): 10A RMS
- Fast switching time: 10µs to open, 10µs to close
- Low-profile 6.5 mm x 6.0 mm QFN package
- Key Application: Replacement of EMR & solid-state relays, solid state circuit breakers. Load controllers for buildings

Menlo MM9200 Product Brief (menlomicro.com)

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Pin Name	Description
GATE (G)	Gate control to turn switch on/off, referenced to MIDPOINT pin.
MIDPOINT (M)	Beams Reference
INPUT (I)	Switch Input Pin
OUTPUT (O)	Switch Output Pin



### Pickering – PXI/PXIe 50 $\Omega$ 4-Channel RF MEMS Multiplexers







### **Performance Characteristics**

What does the Pickering 40/42-878 offer to the user?

- Speed of operation (50 us)
  - EMR solutions, 3 ms (MEMS, 60x faster)
- Long service life (>3 Billion operations)
  - EMR solutions, 10 Million (MEMS, 300x improvement)
- Very low insertion loss (<1.4 dB to 4 GHz)
- Increased frequency (4 GHz Bandwidth)
  - EMR solutions, 3 GHz
- Test system implications:
  - Increases throughput
  - Minimizes downtime
  - Future-proofing







### Technology Comparisons

How does MEMS compare to alternate RF Solutions?

Typical Characteristics		MEMS	EMR	Solid State
MEMS:  Dest fit for long life, cold quitch only with good DE characteristics (incertion loss, signal integrity)	Frequency Range	DC to 4 GHz (usable to 5 GHz)	DC to 3 GHz	10 MHz to 8 GH
and best power handling capability.	Insertion Loss	<1.4 dB to 4 GHz	<1.0 dB to 3 GHz	<6.0 dB to 8 GH
EMR: Best for general purpose, cost-effective, decent life, better tolerance to hot switching, good	VSWR	<1.5:1 to 4 GHz	<1.4:1 to 3 GHz	<1.95:1 to 8 GH
RF characteristics, and power handling capability.	Max RF Power	25 W to 4 GHz	10 W at 3 GHz	4 W at 8 GHz
Solid State: Best for long (indefinite) life when used to spec, AC signals only, some hot switching, a high insertion loss, and low power handling capability.	Operating Time	50 microseconds	3 milliseconds	50 microsecono
*All specifications relate to specific Pickering PXI & PXIe products	Life Expectancy	3 billion operations	10 million operations	Indefinite
	Hot Switching	None	Better tolerance	Some toleranc
	Price per channel normalized to EMR	1.3	1	1.9



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### **Potential Developments**

What Does The Future Hold?

- Higher channel count multiplexers
- Alternate frequencies (to 26 GHz)
- Additional topologies
  - Uncommitted
  - Matrix
  - Fault insertion
- New applications
  - Differential switching









## Thank you.